

Description

The VSM28P06 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is well suited for high current load applications.

Application

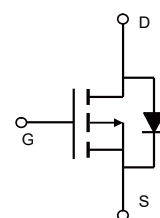
- High side switch for full bridge converter
- DC/DC converter for LCD display

General Features

- $V_{DS} = -60V, I_D = -28A$
- $R_{DS(ON)} < 58m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} < 75m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation



TO-252



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM28P06	VSM28P06-T2	TO-252	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-28	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D(100^\circ C)$	-19.8	A
Pulsed Drain Current	I_{DM}	-112	A
Maximum Power Dissipation	P_D	97	W
Derating factor		0.65	W/ $^\circ C$
Single pulse avalanche energy ^(Note1)	E_{AS}	92	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.55	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient ^(Note 4)	$R_{\theta JA}$	50	$^\circ C/W$

Electrical Characteristics (T_c=25°C unless otherwise noted)

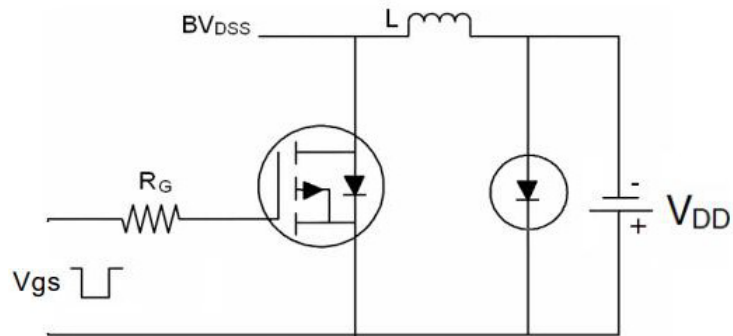
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.7	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	50	58	mΩ
		V _{GS} =-4.5V, I _D =-20A	-	58	75	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-20A	-	20	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, F=1.0MHz	-	2320	-	PF
Output Capacitance	C _{oss}		-	130	-	PF
Reverse Transfer Capacitance	C _{rss}		-	77.3	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V, R _L =1.5Ω, V _{GS} =-10V, R _G =3Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	14	-	nS
Turn-Off Delay Time	t _{d(off)}		-	40	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Q _g	V _{DS} =-30, I _D =-20A, V _{GS} =-10V	-	36.5	-	nC
Gate-Source Charge	Q _{gs}		-	6.7	-	nC
Gate-Drain Charge	Q _{gd}		-	7.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-20A	-	-	-1.2	V
Diode Forward Current	I _S		-	-	-28	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =- 20A di/dt = -100A/μs	-	34	-	nS
Reverse Recovery Charge	Q _{rr}		-	40	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

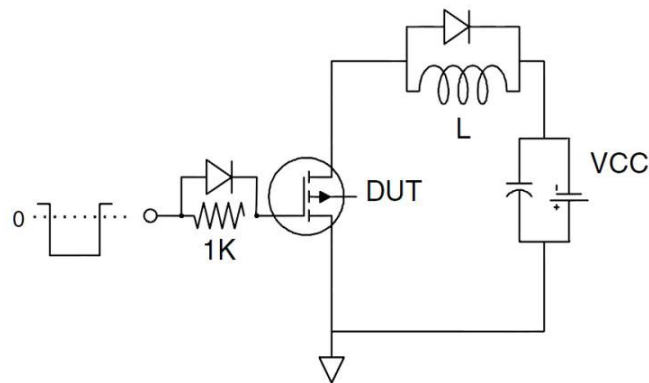
1. EAS condition : T_j=25°C, V_{DD}=-30V, V_G=-10V, L=0.5mH, R_G=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.
4. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

Test Circuit

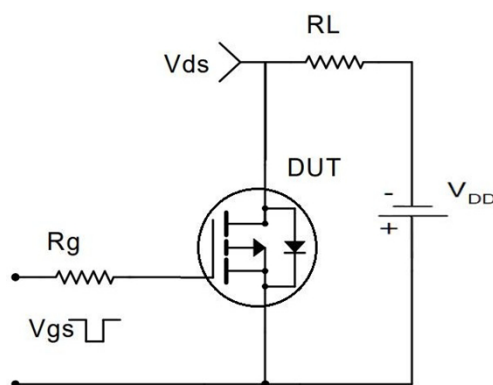
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

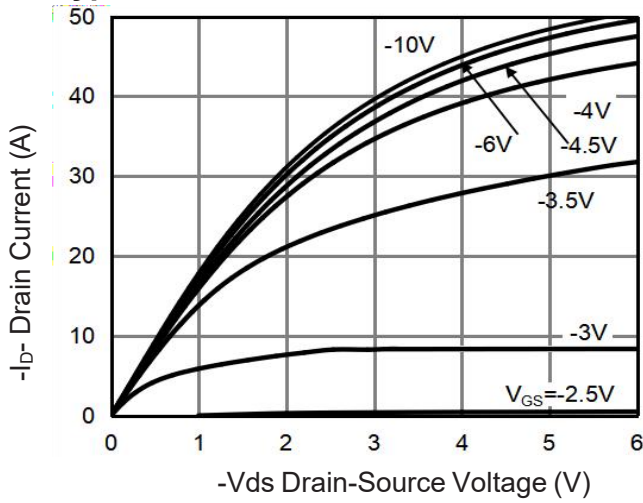


Figure 1 Output Characteristics

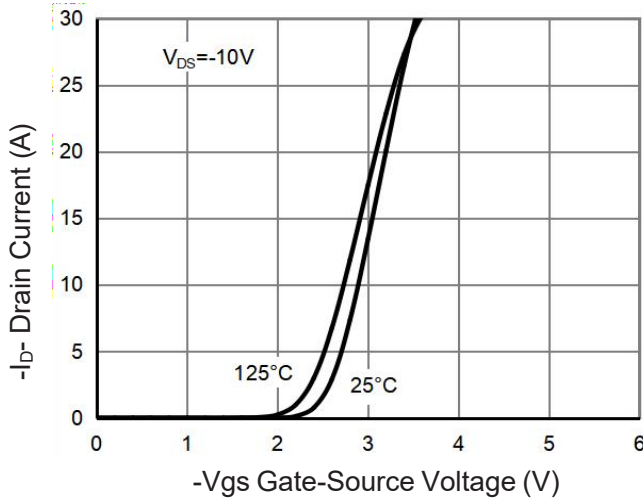


Figure 2 Transfer Characteristics

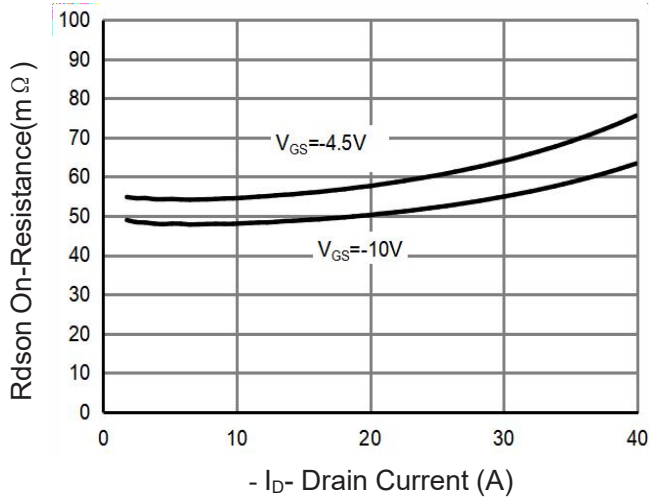


Figure 3 Rdson- Drain Current

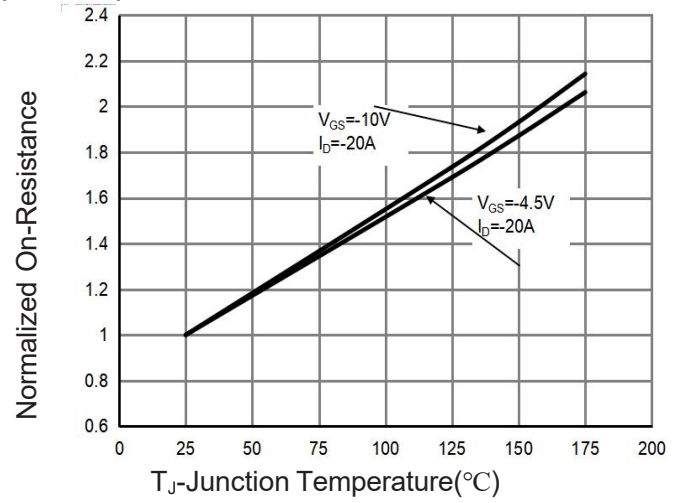


Figure 4 Rdson-Junction Temperature

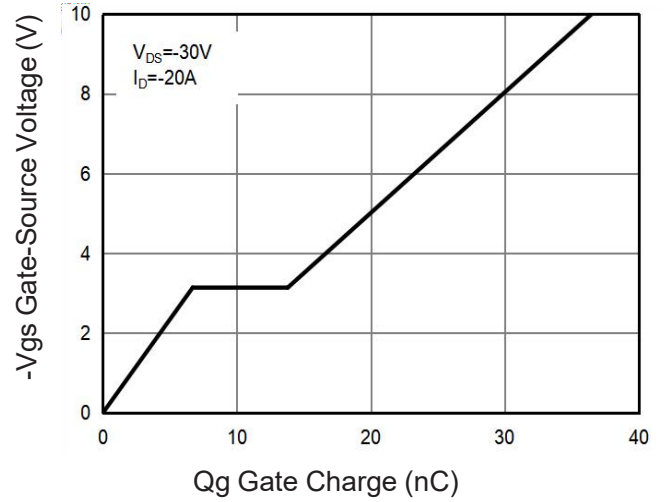


Figure 5 Gate Charge

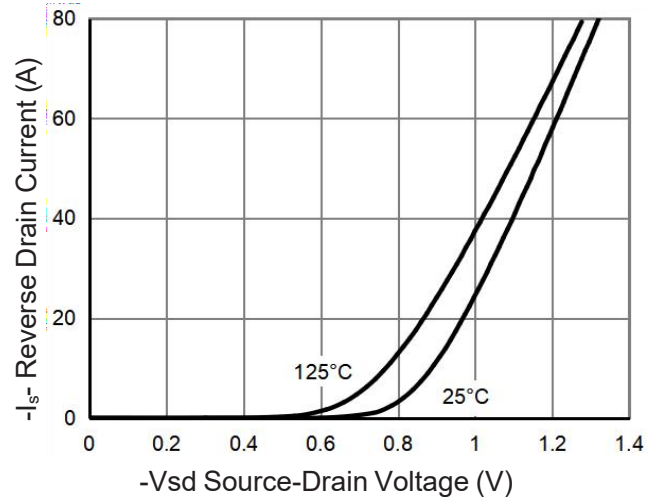
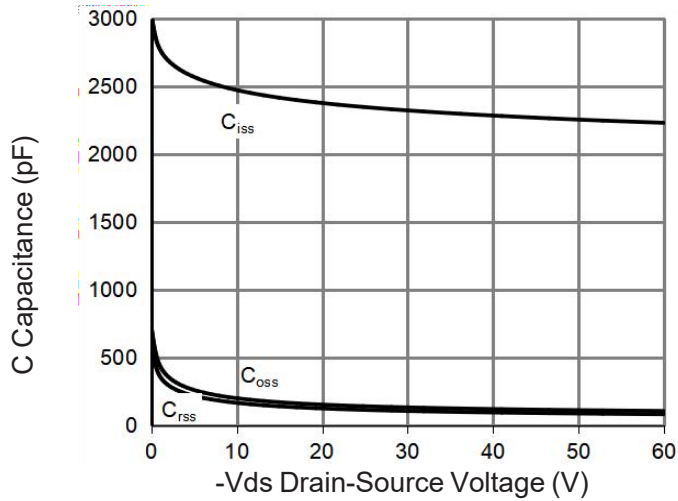
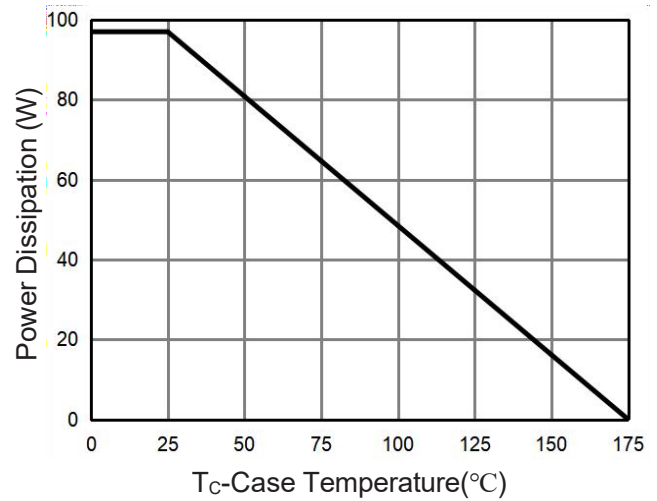
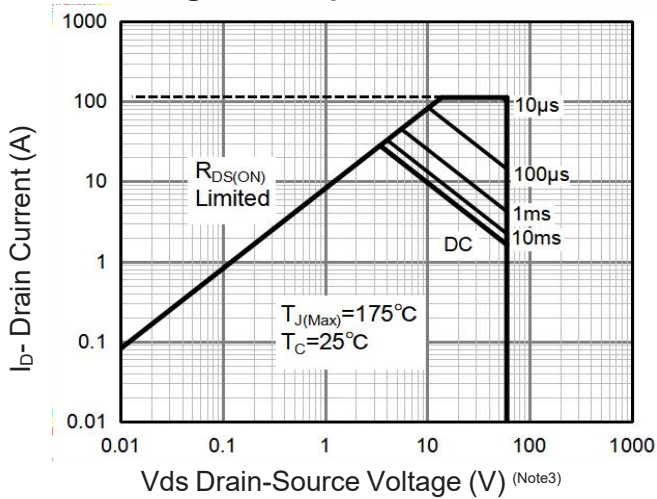
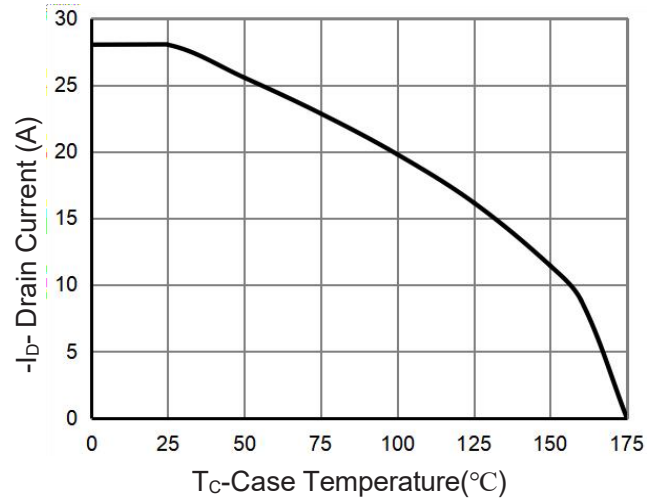
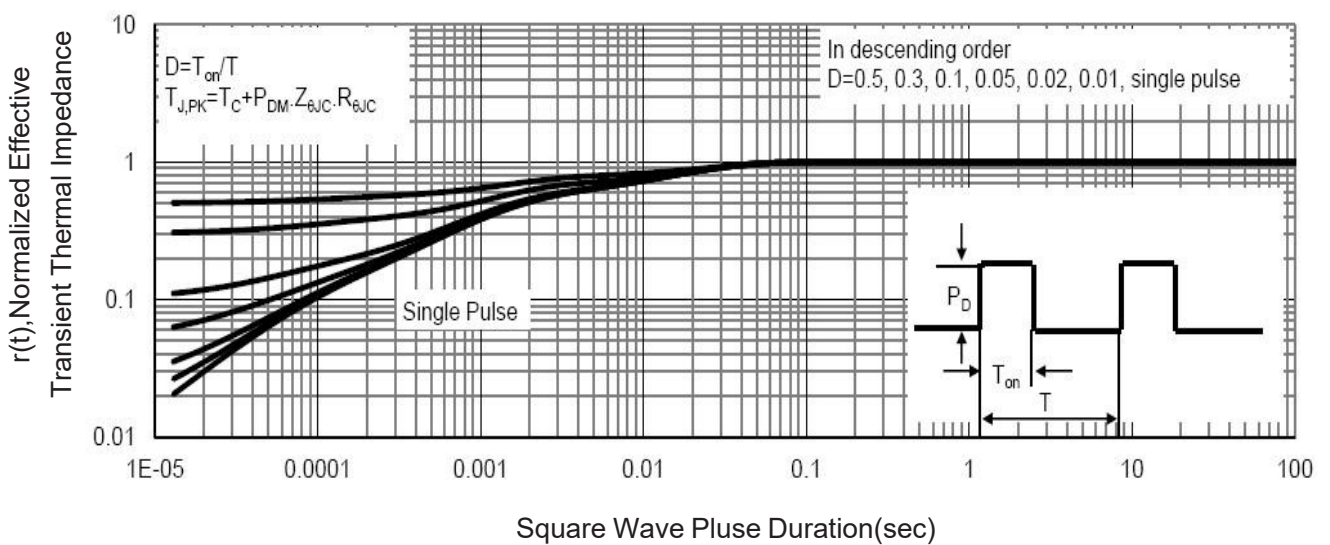


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 ID Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance